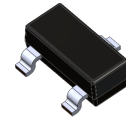
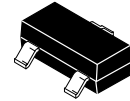


# High-Voltage General-Purpose Diode

## MMBD1401A, MMBD1403A, MMBD1404A, MMBD1405A



SOT-23  
CASE 318BM



SOT-23  
CASE 318-08

### Description

Sourced from process 2V.

### ABSOLUTE MAXIMUM RATINGS

( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Notes 1, 2)

Rating	Symbol	Value	Unit
Working Inverse Voltage	$W_{IV}$	175	V
Average Rectified Current	$I_O$	200	mA
DC Forward Current	$I_F$	600	mA
Recurrent Peak Forward Current	$i_f$	700	mA
Non-Repetitive Peak Forward Surge Current	$i_{f(\text{surge})}$		A
Pulse Width = 1.0 second		1.0	
Pulse Width = 1.0 microsecond		2.0	
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.

### THERMAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted) (Note 3)

Characteristic	Symbol	Value	Unit
Power Dissipation	$P_D$	350	mW
Derate Above $25^\circ\text{C}$		2.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$

- Device is mounted on glass epoxy PCB 1.6 inch  $\times$  1.6 inch  $\times$  0.06 inch, mounting pad for the collector lead minimum 0.93 in<sup>2</sup>.

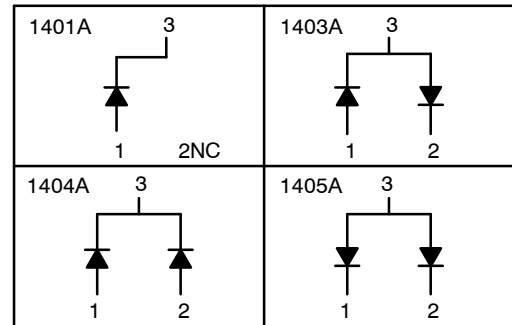
### ELECTRICAL CHARACTERISTICS

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

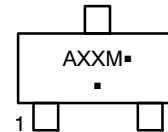
Parameter	Symbol	Condition	Min	Max	Unit
Breakdown Voltage	$B_V$	$I_R = 100 \mu\text{A}$	250	-	V
Reverse Current	$I_R$	$V_R = 120 \text{ V}$	-	40	nA
		$V_R = 175 \text{ V}$	-	100	nA
Forward Voltage	$V_F$	$I_F = 10 \text{ mA}$	-	800	mV
		$I_F = 50 \text{ mA}$	760	920	mV
		$I_F = 200 \text{ mA}$	-	1.1	V
		$I_F = 300 \text{ mA}$	-	1.25	V
Diode Capacitance	$C_O$	$V_R = 0, f = 1.0 \text{ MHz}$	-	2.0	pF
Reverse Recovery Time	$t_{rr}$	$I_F = I_R = 30 \text{ mA},$ $I_{RR} = 3.0 \text{ mA},$ $R_L = 100 \Omega$	-	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

### CONNECTION DIAGRAMS



### MARKING DIAGRAM



AXX = Specific Device Code  
XX = 29/32/33/34  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MMBD1401A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBD1403A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBD1404A	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBD1405A	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

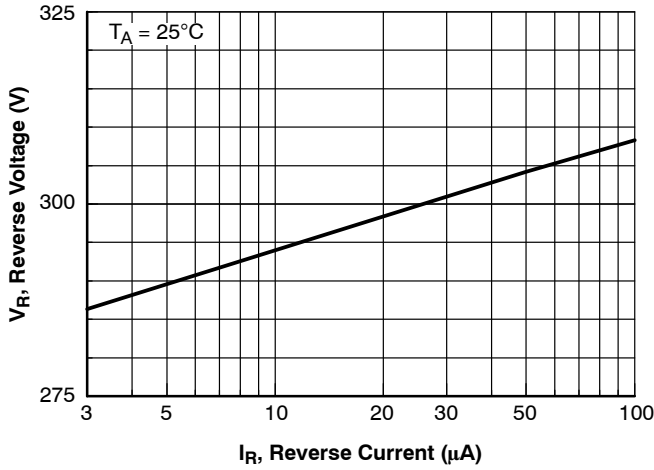


Figure 1. Reverse Voltage vs. Reverse Current  
 $B_V - 1.0$  to  $100 \mu\text{A}$

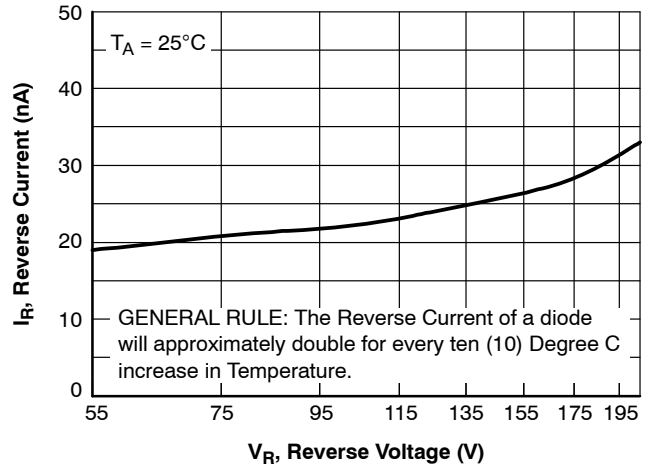


Figure 2. Reverse Current vs. Reverse Voltage  
 $I_R - 55$  to  $205 \text{ V}$

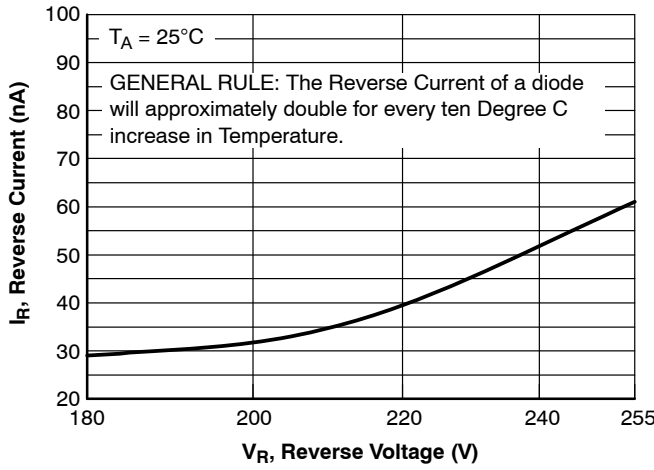


Figure 3. Reverse Current vs. Reverse Voltage  
 $I_R - 180$  to  $255 \text{ V}$

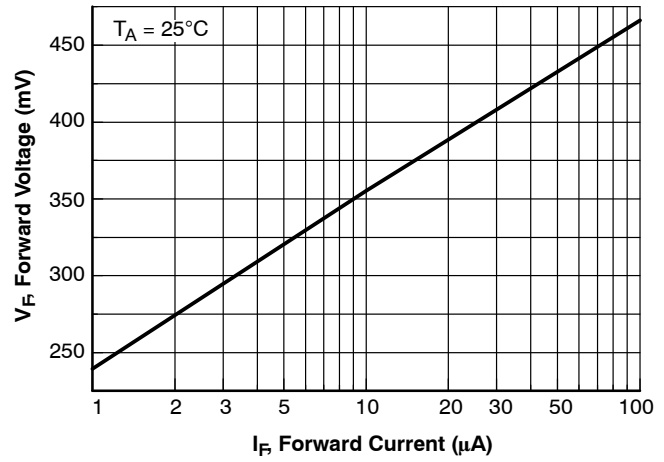


Figure 4. Forward Voltage vs. Forward Current  
 $V_F - 1.0$  to  $100 \mu\text{A}$

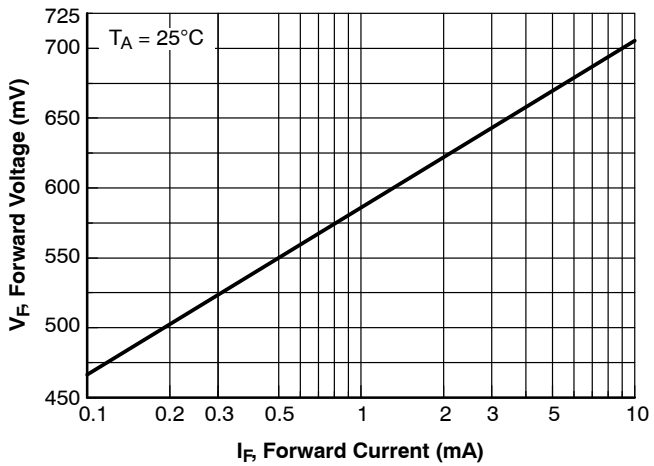


Figure 5. Forward Voltage vs. Forward Current  
 $V_F - 0.1$  to  $10 \text{ mA}$

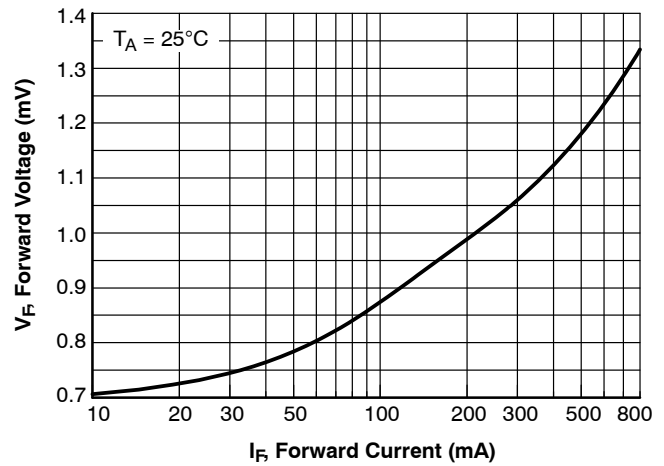


Figure 6. Forward Voltage vs. Forward Current  
 $V_F - 10$  to  $800 \text{ mA}$

TYPICAL CHARACTERISTICS (Continued)

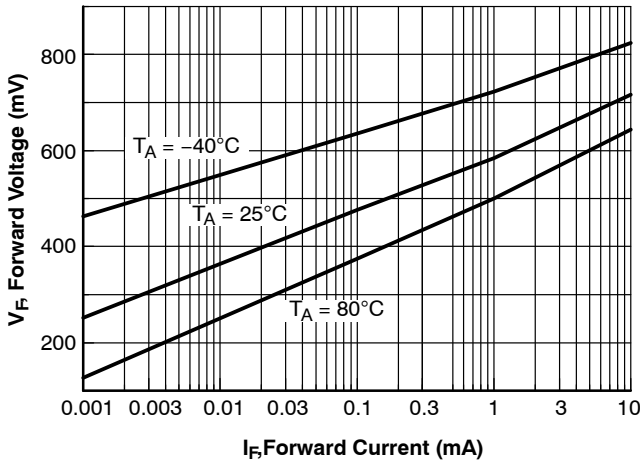


Figure 7. Forward Voltage vs. Ambient Temperature,  $V_F - 1.0 \mu\text{A} - 10 \text{ mA} (-40 \text{ to } +80^\circ\text{C})$

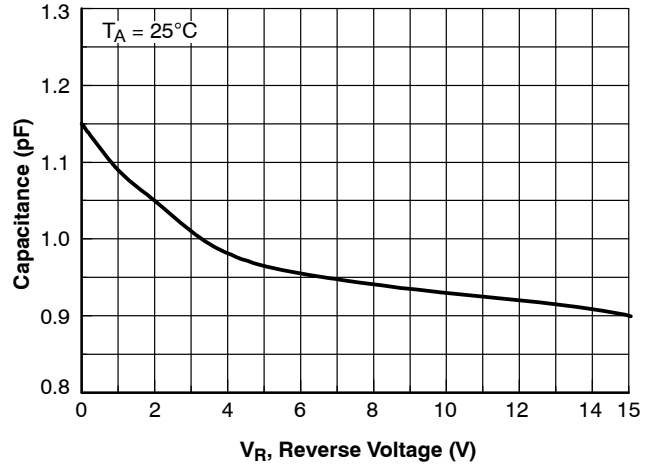


Figure 8. Capacitance vs. Reverse Voltage

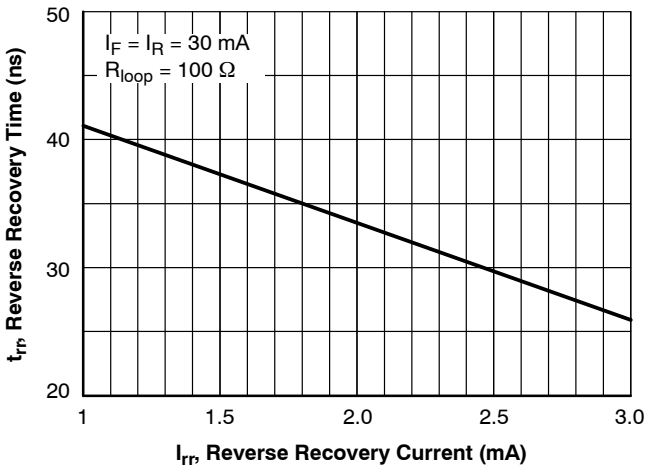


Figure 9. Reverse Recovery Time vs. Reverse Recovery Current ( $I_{rr}$ )

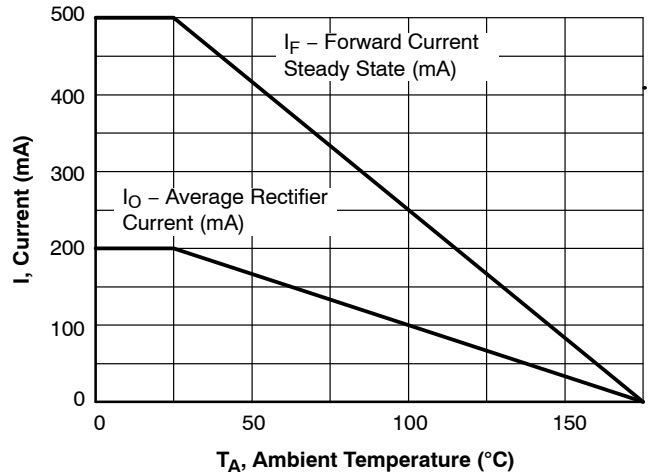


Figure 10. Average Rectified Current ( $I_O$ ) and Forward Current ( $I_F$ ) vs. Ambient Temperature ( $T_A$ )

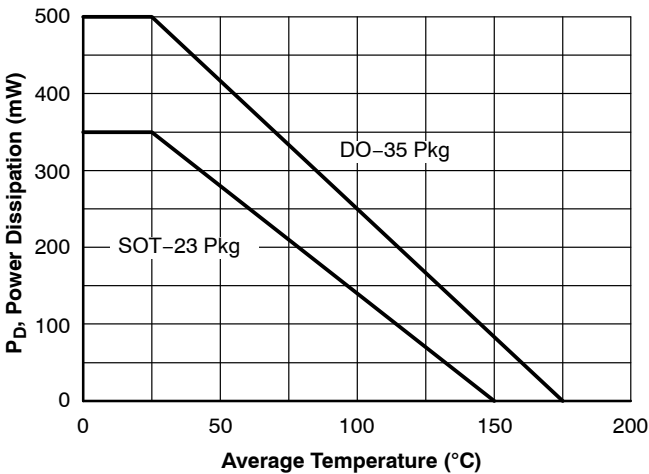
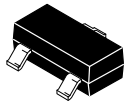


Figure 11. Power Derating Curve

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

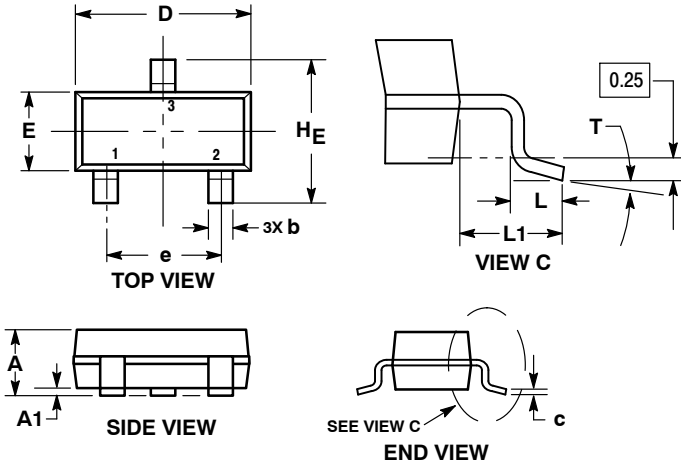
ON Semiconductor®



**SOT-23 (TO-236)**  
**CASE 318-08**  
**ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1

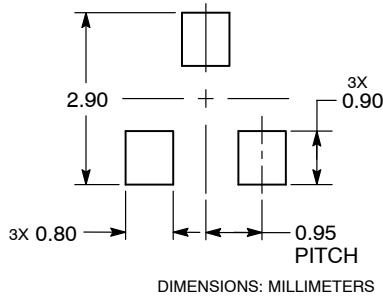


**NOTES:**

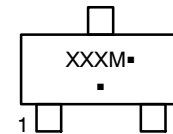
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
 M = Date Code  
 ■ = Pb-Free Package

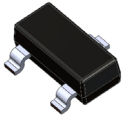
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

- |   |   |   |  |
|---|---|---|--|
| STYLE 1 THRU 5:<br>CANCELLED                                | STYLE 6:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR       | STYLE 7:<br>PIN 1. EMITTER<br>2. BASE<br>3. COLLECTOR       | STYLE 8:<br>PIN 1. ANODE<br>2. NO CONNECTION<br>3. CATHODE |
| STYLE 9:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE          | STYLE 10:<br>PIN 1. DRAIN<br>2. SOURCE<br>3. GATE           | STYLE 11:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE-ANODE | STYLE 12:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE      |
| STYLE 13:<br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE           | STYLE 14:<br>PIN 1. CATHODE<br>2. GATE<br>3. ANODE          | STYLE 15:<br>PIN 1. GATE<br>2. CATHODE<br>3. ANODE          | STYLE 16:<br>PIN 1. ANODE<br>2. CATHODE<br>3. CATHODE      |
| STYLE 17:<br>PIN 1. NO CONNECTION<br>2. ANODE<br>3. CATHODE | STYLE 18:<br>PIN 1. NO CONNECTION<br>2. CATHODE<br>3. ANODE | STYLE 19:<br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE-ANODE | STYLE 20:<br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE         |
| STYLE 21:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN           | STYLE 22:<br>PIN 1. RETURN<br>2. OUTPUT<br>3. INPUT         | STYLE 23:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE         | STYLE 24:<br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE          |
| STYLE 25:<br>PIN 1. ANODE<br>2. CATHODE<br>3. GATE          | STYLE 26:<br>PIN 1. CATHODE<br>2. ANODE<br>3. NO CONNECTION | STYLE 27:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. CATHODE     | STYLE 28:<br>PIN 1. ANODE<br>2. ANODE<br>3. ANODE          |

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<b>DESCRIPTION:</b>	<b>SOT-23 (TO-236)</b>	<b>PAGE 1 OF 1</b>

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

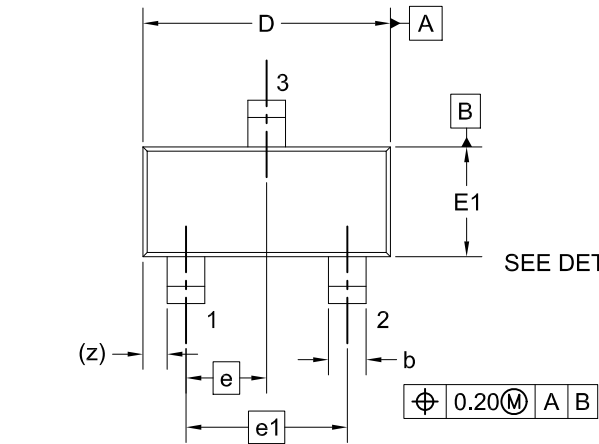


**SOT-23**  
**CASE 318BM**  
**ISSUE A**

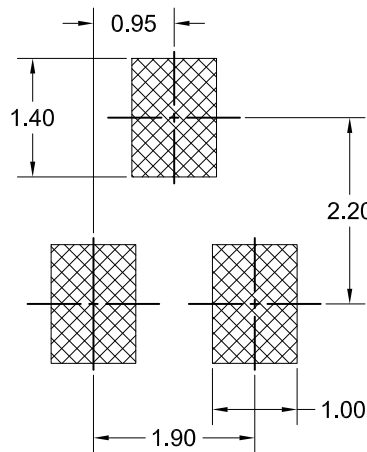
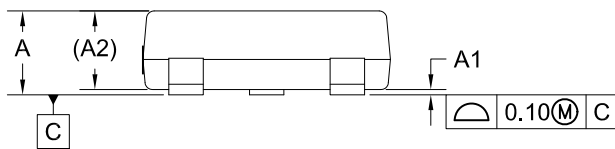
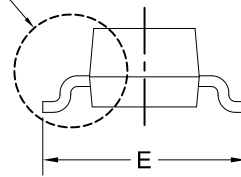
DATE 01 SEP 2021

NOTES: UNLESS OTHERWISE SPECIFIED

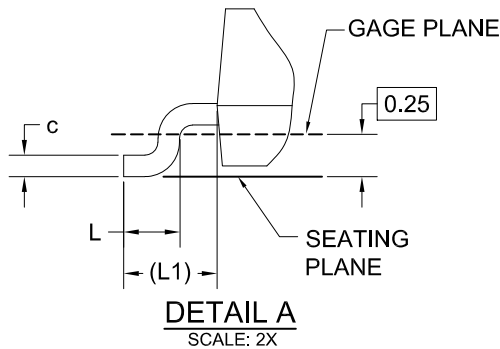
- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.



SEE DETAIL A



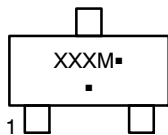
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	MIN.	NOM.	MAX.
A	---	---	1.20
A1	0.00	0.05	0.10
A2	0.93 REF		
b	0.37	0.44	0.60
c	0.08	0.15	0.23
D	2.72	2.92	3.12
E	2.10	2.40	2.70
E1	1.15	1.30	1.50
e	0.95 BSC		
e1	1.90 BSC		
L	0.20	---	---
L1	0.55 REF		
z	0.29 REF		



LAND PATTERN  
RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

### GENERIC MARKING DIAGRAM\*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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